

TOSHIBA Field Effect Transistor Silicon P-Channel MOS Type (U-MOSIV)

## TPC6108

Notebook PC Applications

Portable Equipment Applications

- Small footprint due to small and thin package
- Low drain-source ON-resistance:  $R_{DS(ON)} = 50 \text{ m}\Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 7.4 \text{ S}$  (typ.)
- Low leakage current:  $I_{DSS} = -10 \text{ }\mu\text{A}$  (max) ( $V_{DS} = -30 \text{ V}$ )
- Enhancement mode:  $V_{th} = -0.8 \text{ to } -2.0 \text{ V}$  ( $V_{DS} = -10 \text{ V}$ ,  $I_D = -1 \text{ mA}$ )

### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Characteristics		Symbol	Rating	Unit
Drain-source voltage		$V_{DSS}$	-30	V
Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ )		$V_{DGR}$	-30	V
Gate-source voltage		$V_{GSS}$	$\pm 20$	V
Drain current	DC (Note 1)	$I_D$	-4.5	A
	Pulse (Note 1)	$I_{DP}$	-18	
Drain power dissipation ( $t = 5 \text{ s}$ ) (Note 2a)		$P_D$	2.2	W
Drain power dissipation ( $t = 5 \text{ s}$ ) (Note 2b)		$P_D$	0.7	
Single-pulse avalanche energy (Note 3)		$E_{AS}$	1.3	mJ
Avalanche current		$I_{AR}$	-2.25	A
Repetitive avalanche energy Single-device value at dual operation (Note 4)		$E_{AR}$	0.22	mJ
Channel temperature		$T_{ch}$	150	$^\circ\text{C}$
Storage temperature range		$T_{stg}$	-55 to 150	$^\circ\text{C}$

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

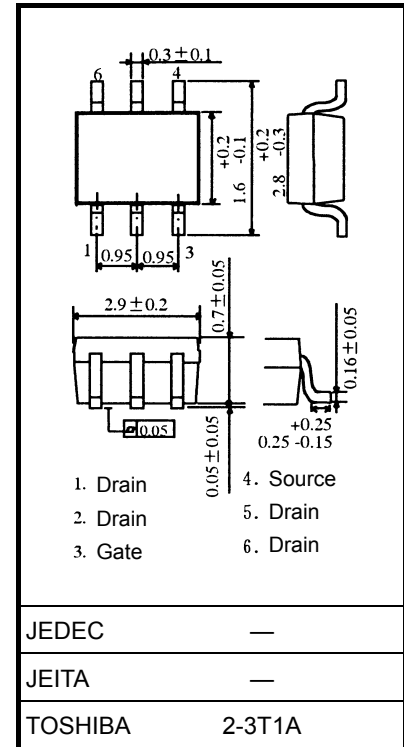
### Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient ( $t = 5 \text{ s}$ ) (Note 2a)	$R_{th(ch-a)}$	56.8	$^\circ\text{C/W}$
Thermal resistance, channel to ambient ( $t = 5 \text{ s}$ ) (Note 2b)	$R_{th(ch-a)}$	178.5	$^\circ\text{C/W}$

Note: For Notes 1 to 5, see page 3.

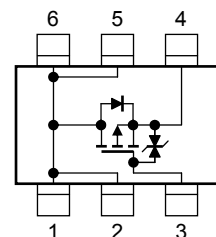
Caution: This transistor is an electrostatic-sensitive device. Handle with care.

Unit: mm

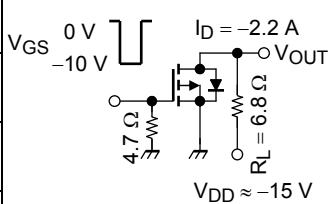


Weight: 0.011 g (typ.)

### Circuit Configuration



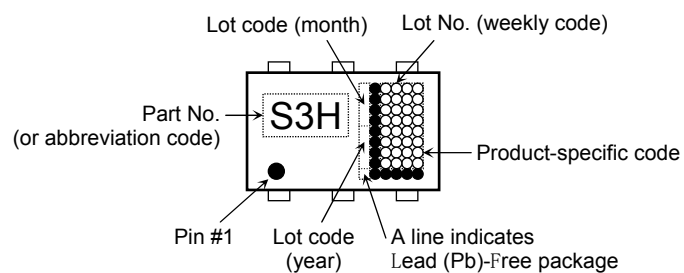
## Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	V <sub>GS</sub> = ±16 V, V <sub>DS</sub> = 0 V	—	—	±10	μA
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = -30 V, V <sub>GS</sub> = 0 V	—	—	-10	μA
Drain-source breakdown voltage		V <sub>(BR)</sub> DSS	I <sub>D</sub> = -10 mA, V <sub>GS</sub> = 0 V	-30	—	—	V
		V <sub>(BR)</sub> DSX	I <sub>D</sub> = -10 mA, V <sub>GS</sub> = 20 V	-15	—	—	
Gate threshold voltage		V <sub>th</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -1 mA	-0.8	—	-2.0	V
Drain-source ON-resistance		R <sub>DS</sub> (ON)	V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -2.2 A	—	75	100	mΩ
		R <sub>DS</sub> (ON)	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -2.2 A	—	50	60	
Forward transfer admittance		Y <sub>fs</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -2.2 A	3.7	7.4	—	S
Input capacitance		C <sub>iss</sub>	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	—	570	—	pF
Reverse transfer capacitance		C <sub>rss</sub>		—	75	—	
Output capacitance		C <sub>oss</sub>		—	85	—	
Switching time	Rise time	t <sub>r</sub>		—	3.5	—	ns
	Turn-on time	t <sub>on</sub>		—	12	—	
	Fall time	t <sub>f</sub>		—	21	—	
	Turn-off time	t <sub>off</sub>		Duty ≤ 1%, t <sub>w</sub> = 10 μs	—	70	
Total gate charge (gate-source plus gate-drain)		Q <sub>g</sub>	V <sub>DD</sub> ≈ -24 V, V <sub>GS</sub> ≈ -10 V, I <sub>D</sub> = -4.5 A	—	13	—	nC
Gate-source charge1		Q <sub>gs1</sub>		—	1.8	—	
Gate-drain (“Miller”) charge		Q <sub>gd</sub>		—	2.5	—	

## Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
Drain reverse current	Pulse (Note 1)	$I_{DRP}$	—	—	—	-18	A
Forward voltage (diode)		$V_{DSF}$	$I_{DR} = -4.5 \text{ A}, V_{GS} = 0 \text{ V}$	—	—	1.2	V

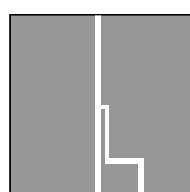
## Marking (Note 5)



Note 1: Ensure that the channel temperature does not exceed 150°C.

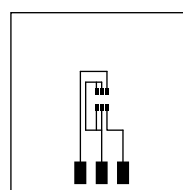
Note 2: (a) Device mounted on a glass-epoxy board (a) (t = 5 s)

(b) Device mounted on a glass-epoxy board (b) (t = 5 s)



(a)

FR-4  
25.4 × 25.4 × 0.8  
(Unit: mm)



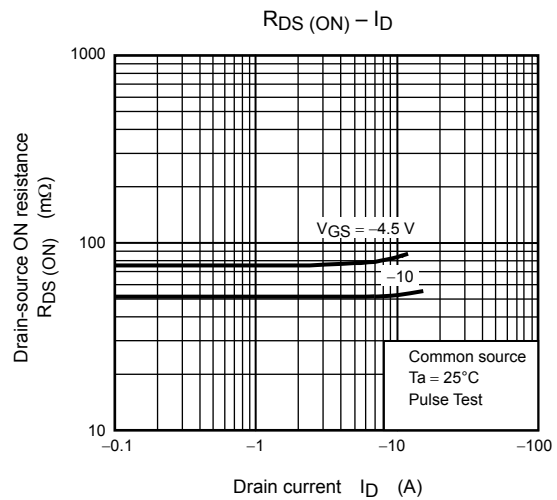
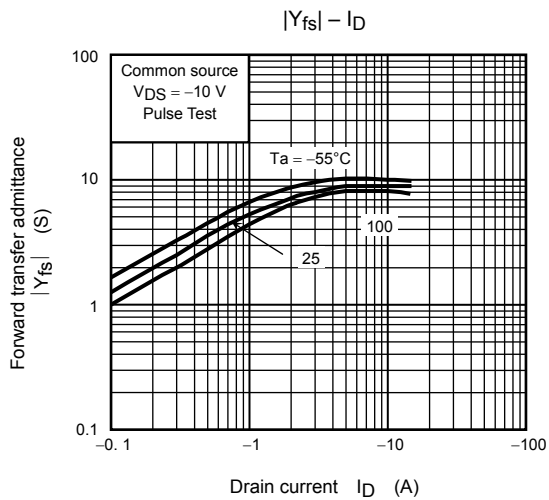
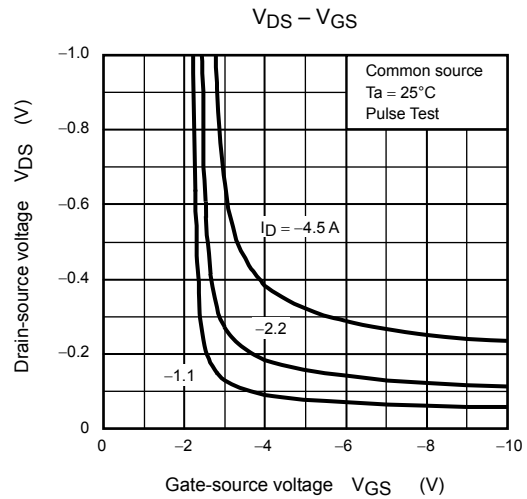
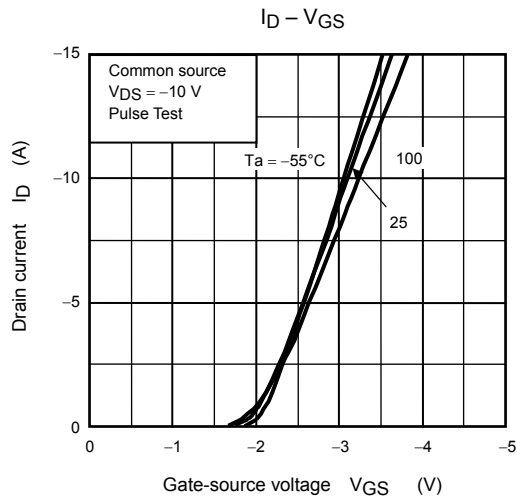
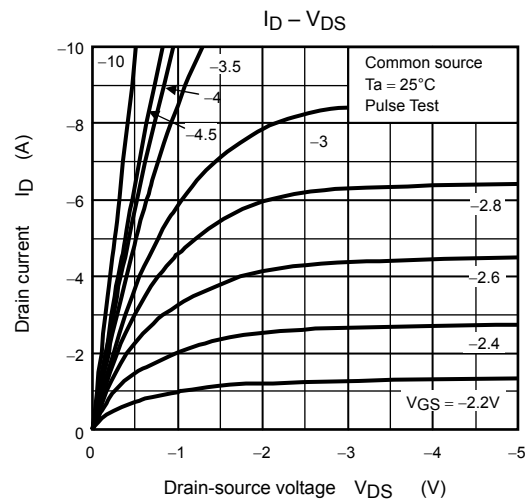
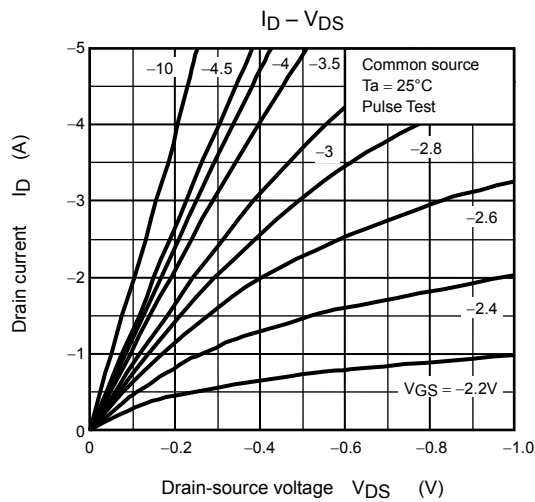
(b)

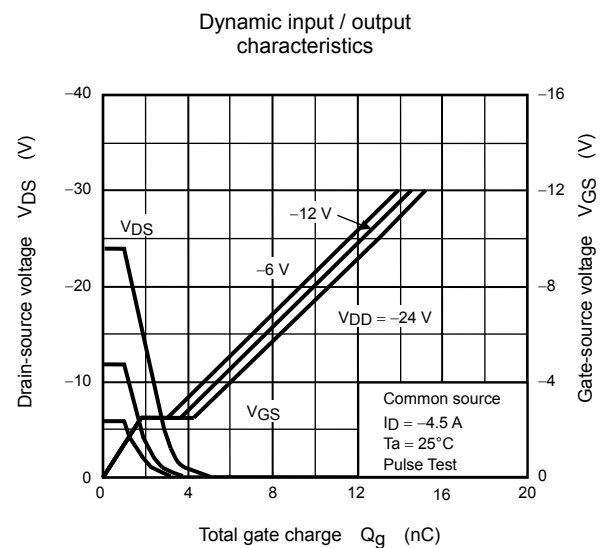
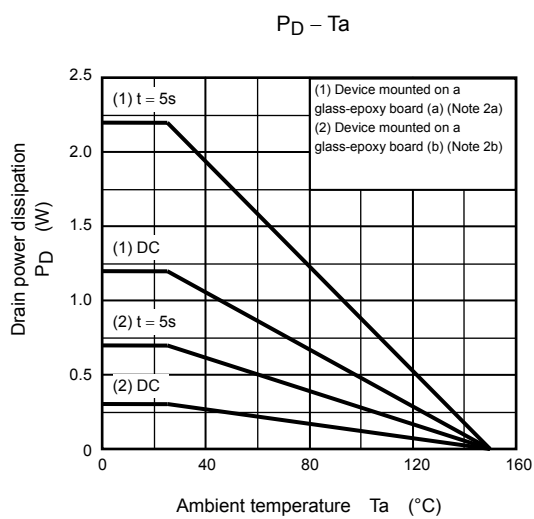
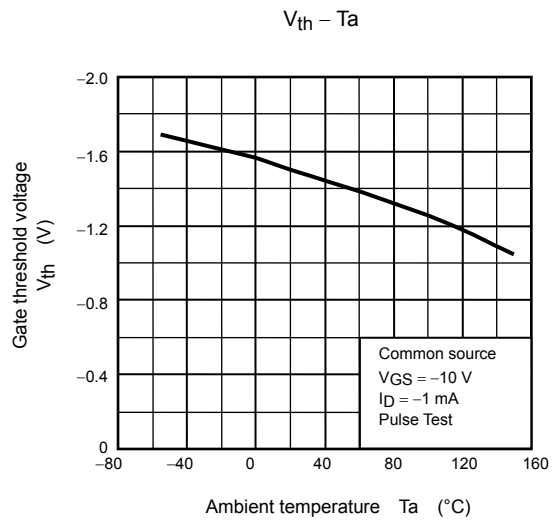
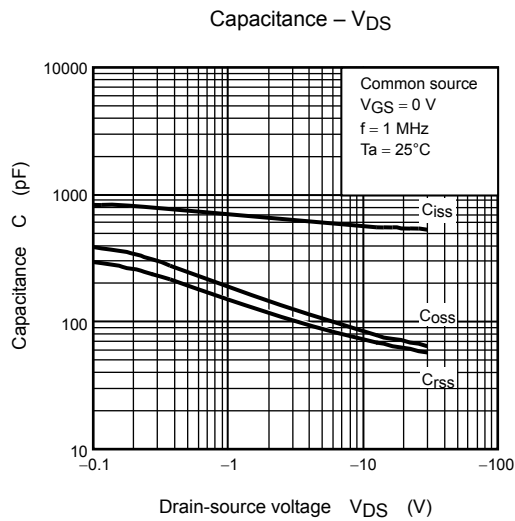
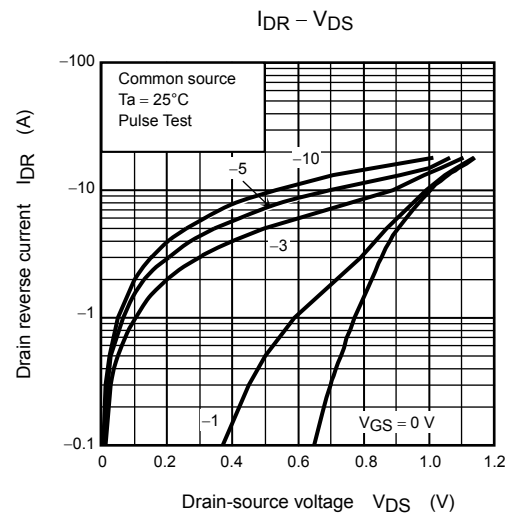
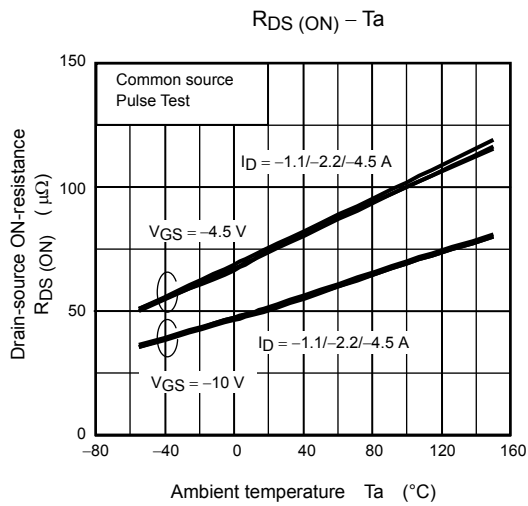
FR-4  
25.4 × 25.4 × 0.8  
(Unit: mm)

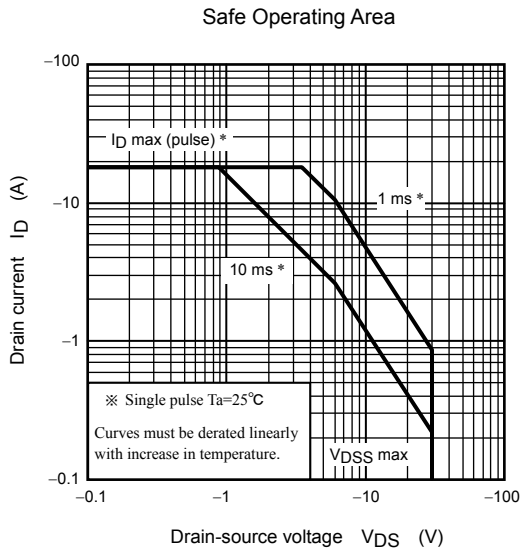
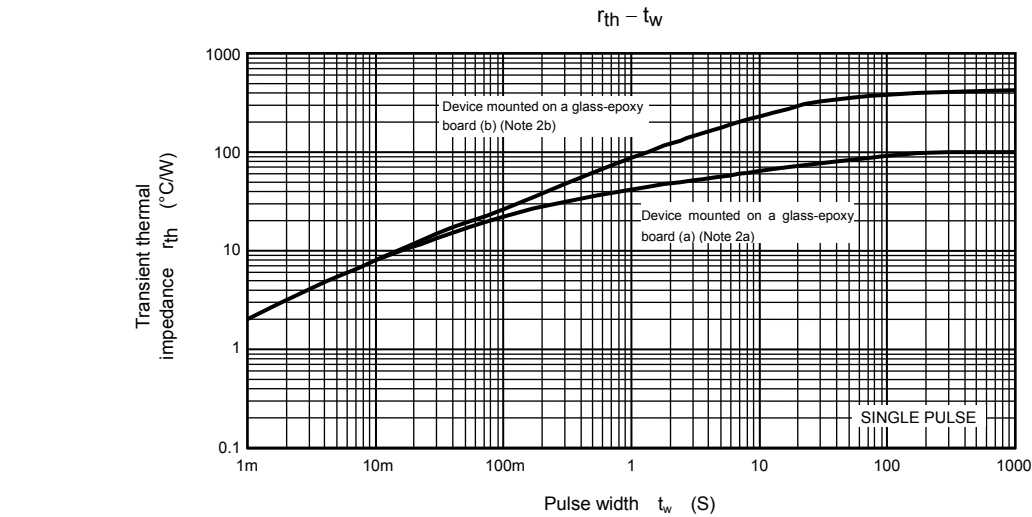
Note 3:  $V_{DD} = -24\text{ V}$ ,  $T_{ch} = 25^\circ\text{C}$  (initial),  $L = 0.2\text{ mH}$ ,  $R_G = 25\ \Omega$ ,  $I_{AR} = -2.25\text{ A}$

Note 4: Repetitive rating: pulse width limited by max channel temperature

Note 5: ● to the lower left of the Part No. marking indicates Pin 1.







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20070701-EN GENERAL

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